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| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Use as many sheets as necessary) |      | <b>Complete if Known</b> |               |
|   |      | Application Number       | 10/821,010    |
|   |      | Filing Date              | April 8, 2004 |
|   |      | First Named Inventor     | Xuming Xiong  |
|   |      | Art Unit                 | 1775 1793     |
|   |      | Examiner Name            | Unassigned    |
| Sheet 1   | of 1 | Attorney Docket Number   | 1014-SP215-US |

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|                                 | A                     | Y. Iijima, et al., "In-Plane Aligned YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> Thin Films Deposited on Polycrystalline Metallic Substrates", Appl. Phys. Letters, Vol. 60, pp. 769-771, 1992.   |                |
|                                 | B                     | X. Wu, et al., "Properties of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-s</sub> Thick Films on Flexible Buffered Metallic Substrates", Appl. Phys. Letters, Vol. 67, No. 16, pp. 2397-2399, 1995.   |                |
|                                 | C                     | H. Freyhardt, et al., "YBaCuO Thick Films on Planar and Curved Technical Substrates", Vol. 7, No. 2, pp. 1426-1431, 1997.   |                |
|                                 | D                     | R. Huehne, et al., "Growth of Biaxial Textured MgO-Layers by Ion-Beam Assisted Pulsed Laser Deposition", Crystal Res. Technology, Vol. 35, No. 4, pp. 419-425, 2000.  |                |
|                                 | E                     | L. Dong, et al., "Texture Development Mechanisms in Ion Beam Assisted Deposition", Journal of Applied Physics, Vol. 84, No. 9, pp. 5261-5269, 1998.   |                |
|                                 | F                     | J. Groves, et al., "Recent Progress in Continuously Processes IBAD MgO Template Meters for HTS Applications, Physica C 382, pp. 43-47, 2002.  |                |
|                                 | G                     | ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /K.M.V./  |                |
|                                 | H                     |   |                |
|                                 | I                     |   |                |
|                                 | J                     |   |                |

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|--------------------|---------------------------|-----------------|------------|
| Examiner Signature | /Kallambella Vijayakumar/ | Date Considered | 10/01/2008 |
|--------------------|---------------------------|-----------------|------------|

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